



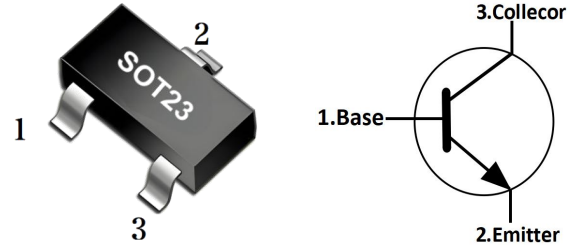
2SC1623

NPN SILICON TRANSISTOR

DESCRIPTION

The 2SC1623 is a NPN silicon transistor using our advanced technology to provide customers with high DC current gain and high breakdown voltage. The 2SC1623 is usually used in audio frequency general purpose amplifier.

The 2SC1623 meet the ROHS and Green Product requirement with full function reliability approved.

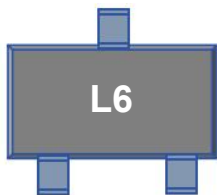


FEATURES

- * High DC current gain : $h_{FE}=200$ (Typ) $V_{CE}=6V, I_C=1mA$
- * High voltage: $V_{CEO}=50V$

MARKING

Type Code: Marking: L6



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-base voltage	60	V
V _{CEO}	Collector-emitter voltage	50	V
V _{EB0}	Emitter-base voltage	5	V
I _c	Collector current	100	mA
P _c	Collector Power Dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C
ROJA	Thermal Resistance From Junction To Ambient	625	°C/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.



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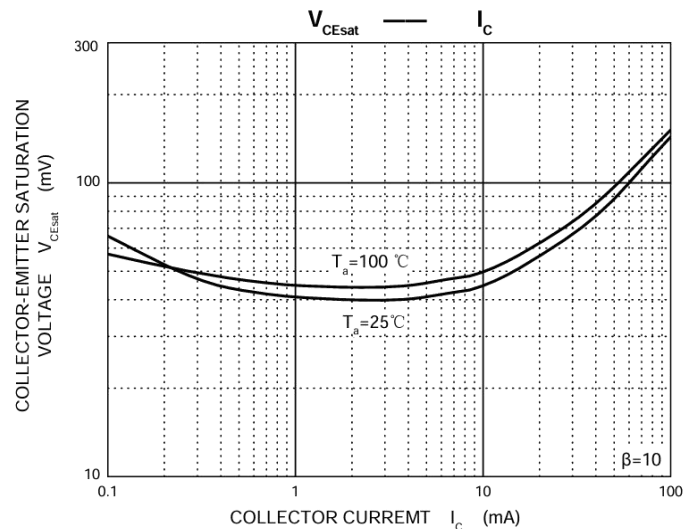
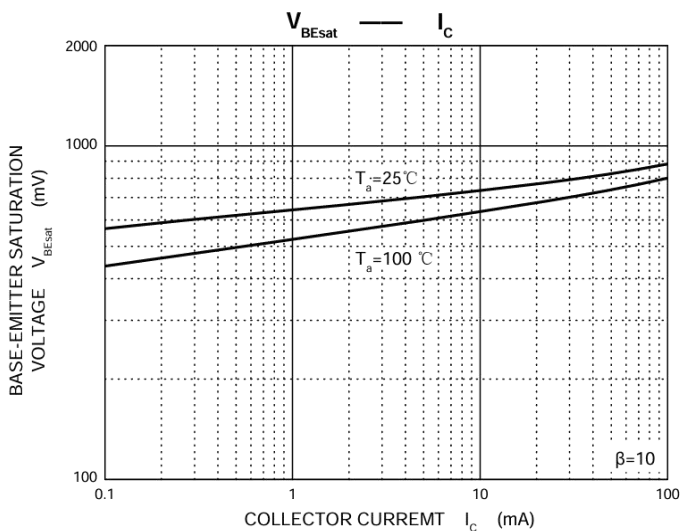
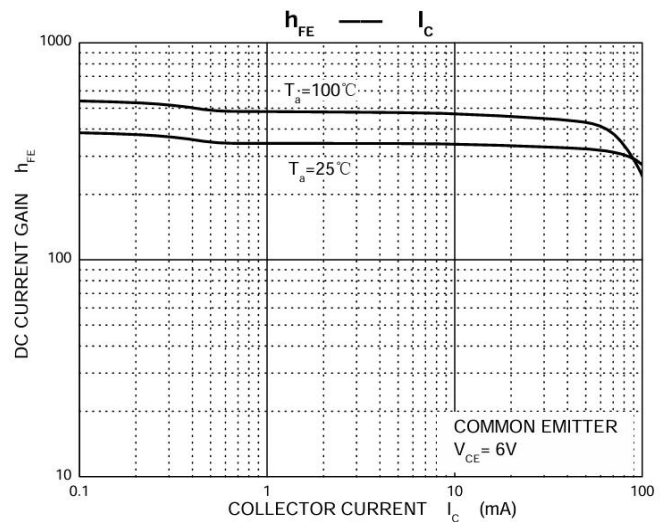
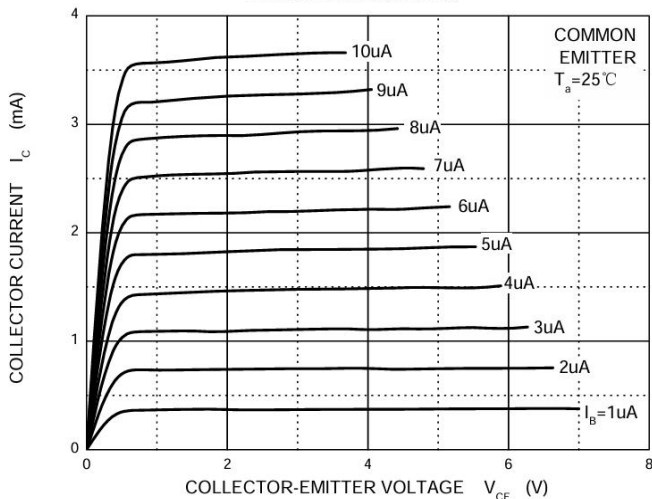
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ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=6V, I_C=10mA$		250		MHz

TYPICAL CHARACTERISTICS

Static Characteristic

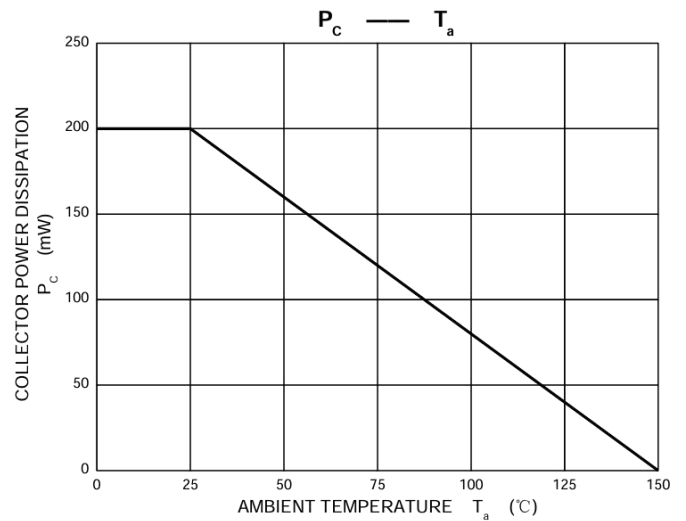
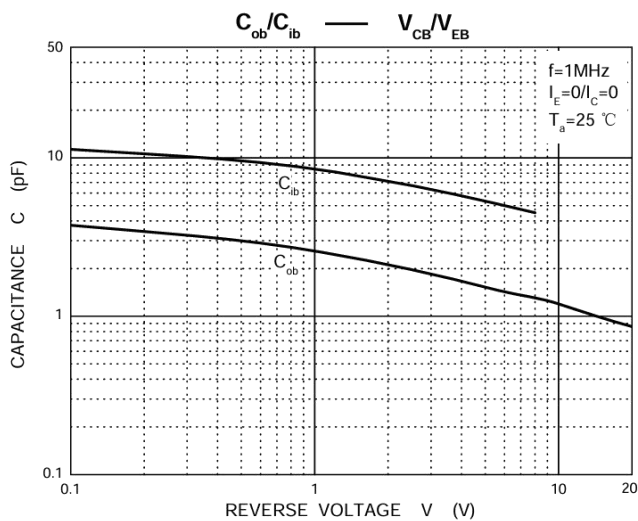
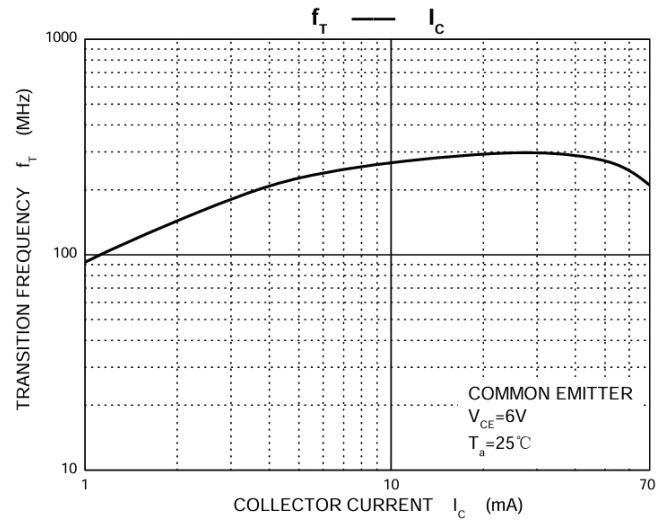
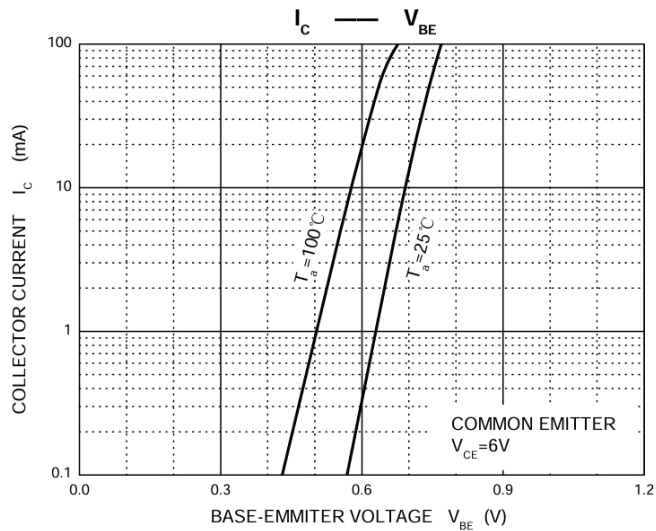




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TYPICAL CHARACTERISTICS(Con.t)

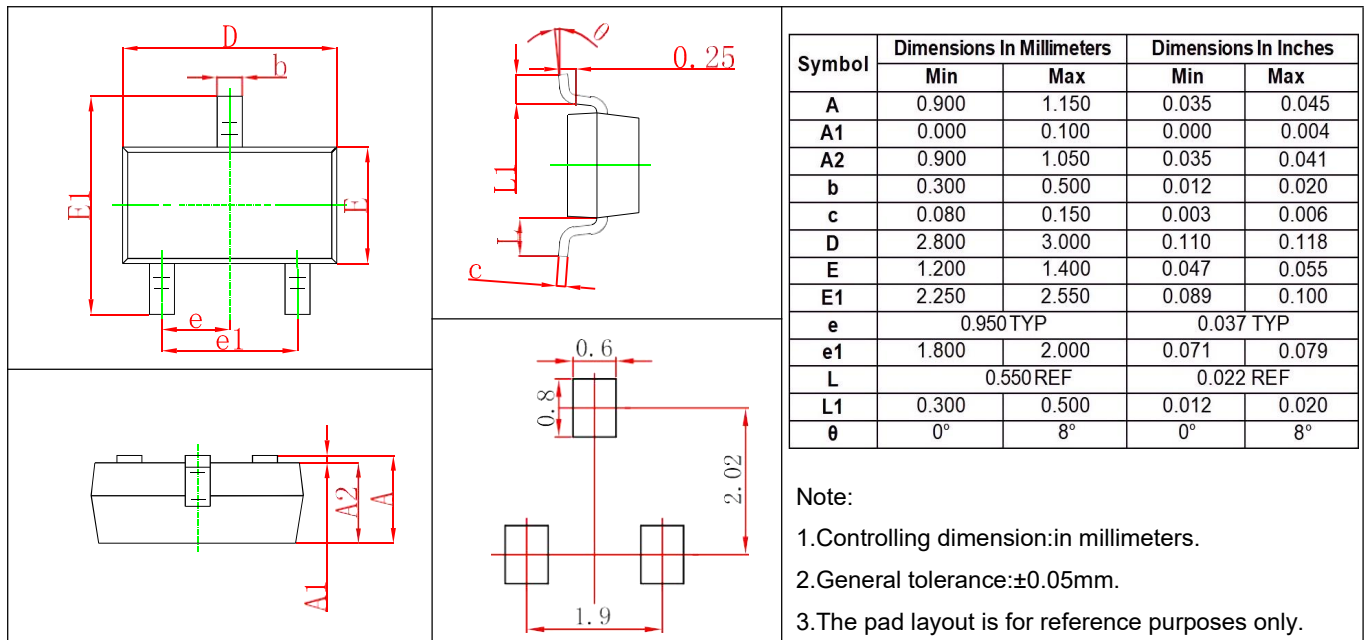




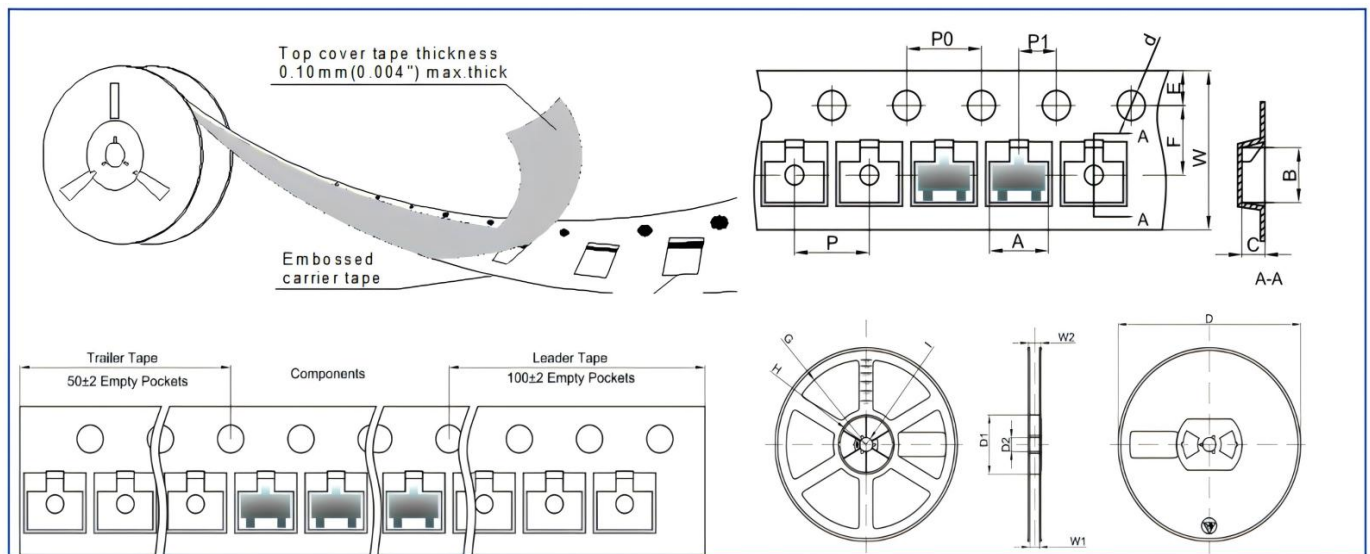
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SOT23 PACKAGE OUTLINE DIMENSIONS



REEL PACKING



Dimensions are in millimeter										
PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.15	2.77	1.22	Φ1.50	1.75	3.50	4.00	4.00	2.00	8.00
Reel Optiom	D	D1	D2	G	H	I	W1	W2	Q.TY PER REEL	
7" Dia	Φ178.0	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	3000PCS	
13" Dia	φ330.0	/	13.00	/	/	R6.50	9.50	12.30	10000PCS	